

A decorative graphic on the left side of the slide consists of a vertical, teardrop-shaped area filled with a complex, multi-colored grid pattern of thin lines in shades of blue, green, yellow, and red.

# **RADAR: RET-Aware Detailed Routing Using Fast Lithography Simulations**

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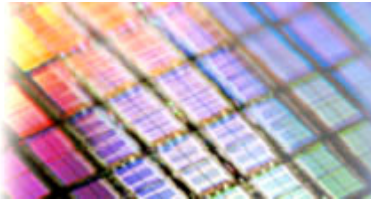
# Outline

- ◆ Lithography Background
- ◆ Motivation
- ◆ Fast Lithography Simulation
- ◆ Edge Placement Error Metric
- ◆ EPE map based detailed routing
- ◆ Results
- ◆ Conclusion

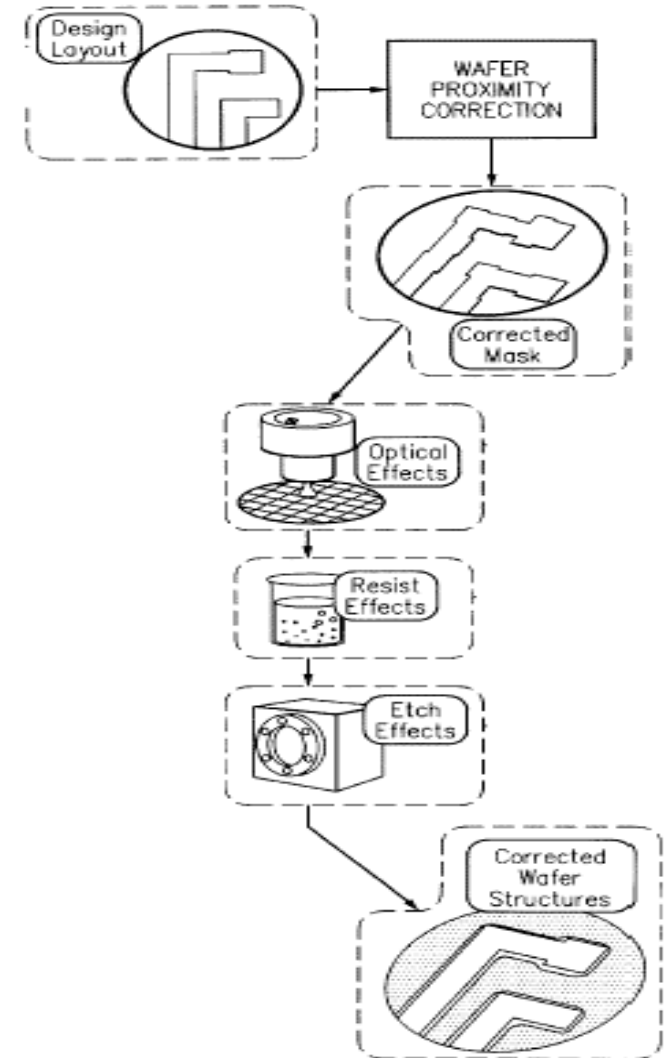
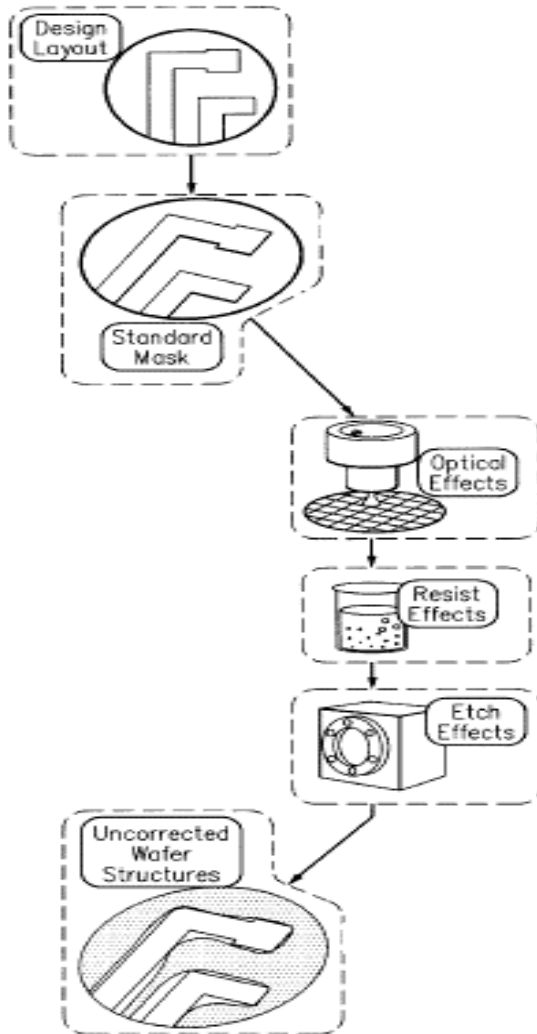


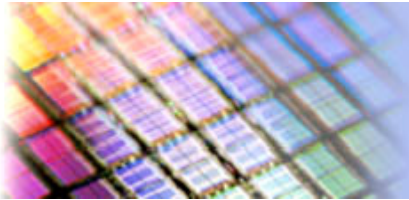
# Litho Background

- ◆ Lithography limitation is a key bottleneck in nanometer manufacturing
- ◆ 193nm wavelength => deep sub-wavelength
- ◆ Need extensive RET
  - > OPC
  - > PSM
  - > OAI
- ◆ However, RETs mostly are done post-layout
- ◆ Major impact from raising the abstraction level  
RET-aware layout optimization => real **D**FM

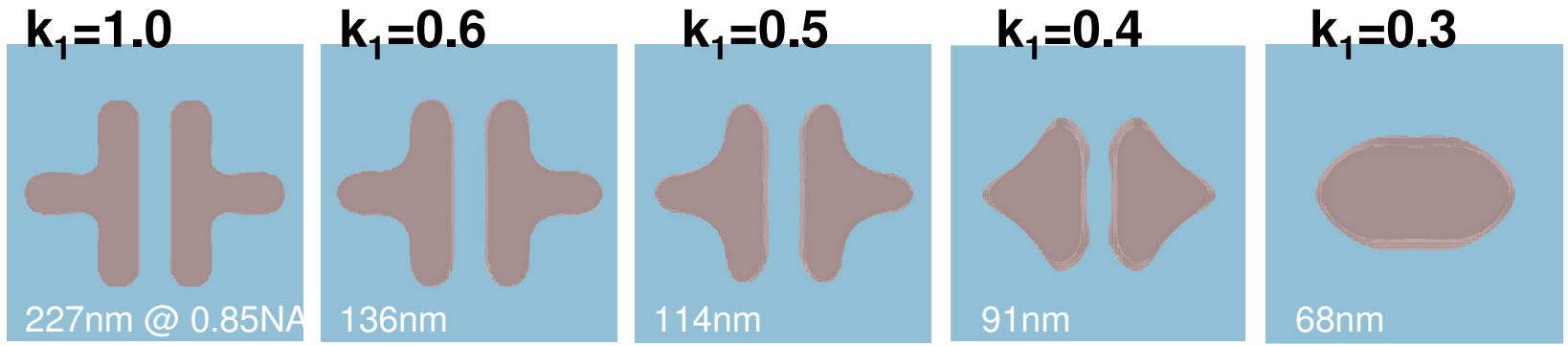


# Lithography process with and without OPC



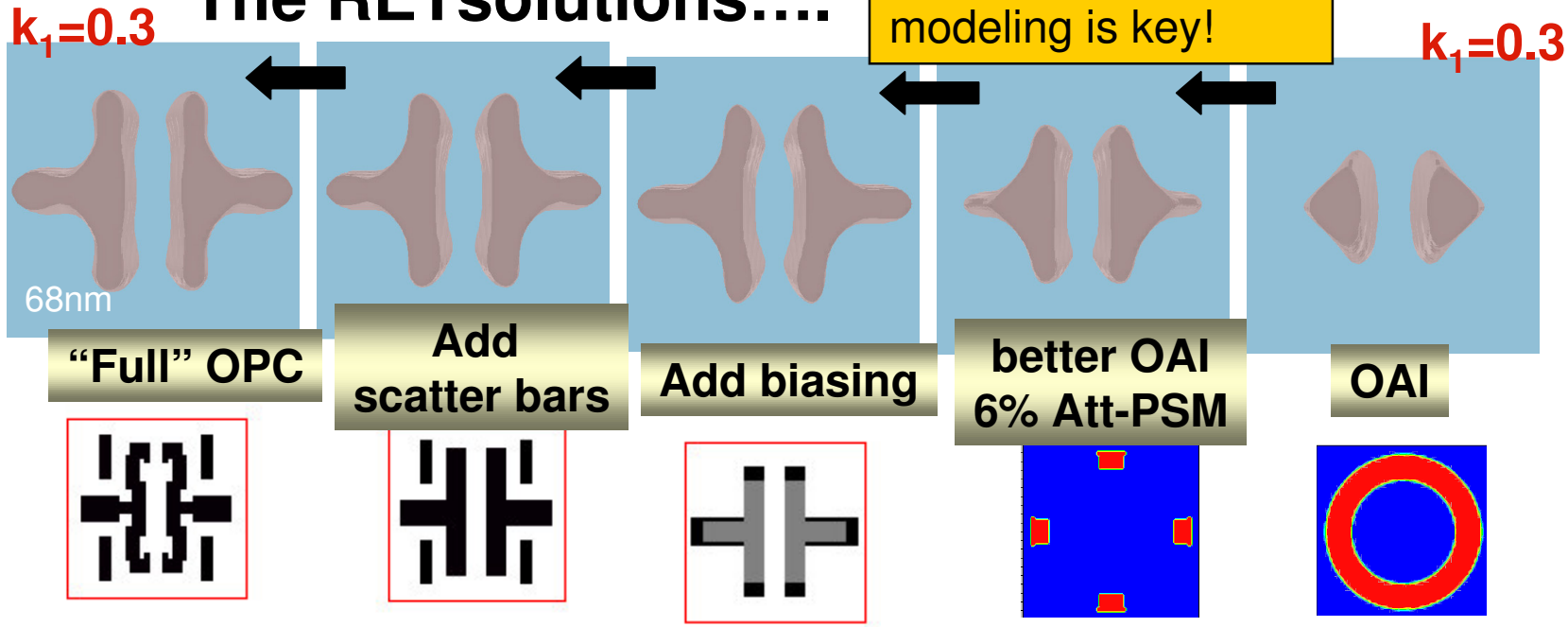


# Lithography and RET



## The RET solutions....

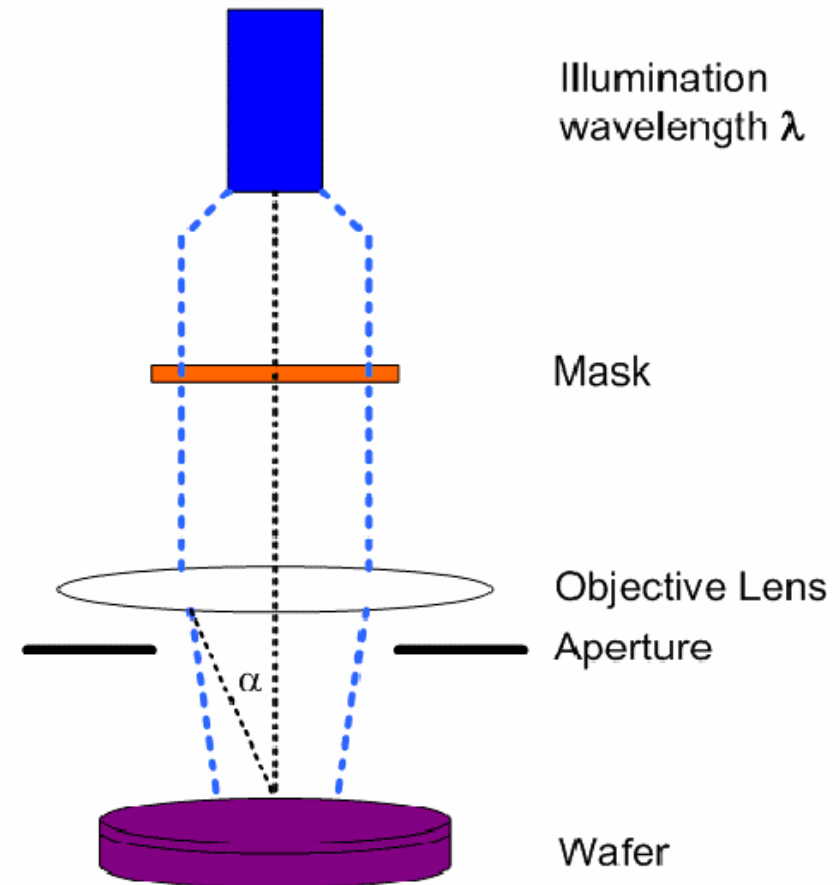
accurate and flexible modeling is key!



(Courtesy ASML)

# Fast Aerial Image Simulation

- ◆ Fast lithography simulation to generate EPE map
- ◆ Aerial image is the first order approximation (resist not considered)
- ◆ Basic principle: pre-compute image density convolution table for fast table lookup





# Aerial Image Simulation

- ◆ For coherent light entering mask:

$$E(x, y) = F^{-1}\{F\{t_m(x, y)\}P(f_x, f_y)\}$$

$E$  = electric field at image point  $(x, y)$

$F, F^{-1}$  = fourier, inverse fourier transforms

$t_m$  = mask transmission function

$P$  = pupil function at objective lens

$f_x, f_y$  = spatial frequencies at image plane

- Intensity equation at image plane

$$I(x, y) = |E(x, y)|^2 = E \bullet E^*$$



## (Cont'd)

- ◆ Using principle of superposition and assuming the optics system is a linear space-invariant system, we get the following convolution:

$$E = T_m \otimes h$$

$T_m$  = mask transmission function

$h$  = impulse response function

$$I = E \bullet E^*$$



## (Cont'd)

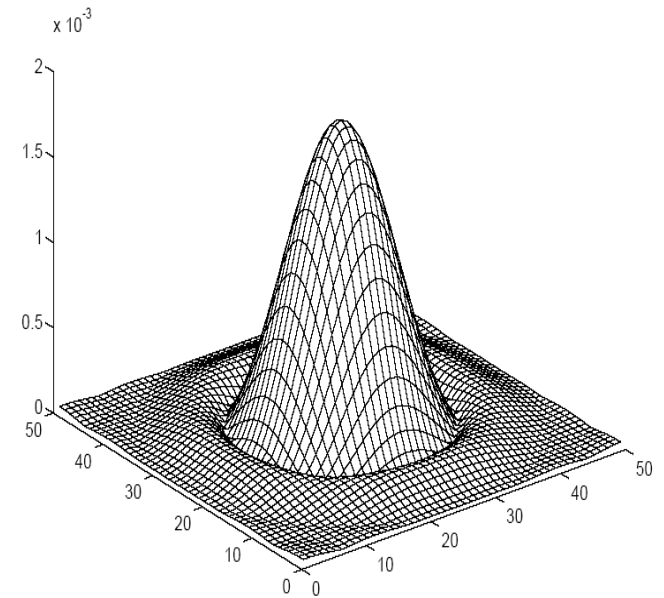
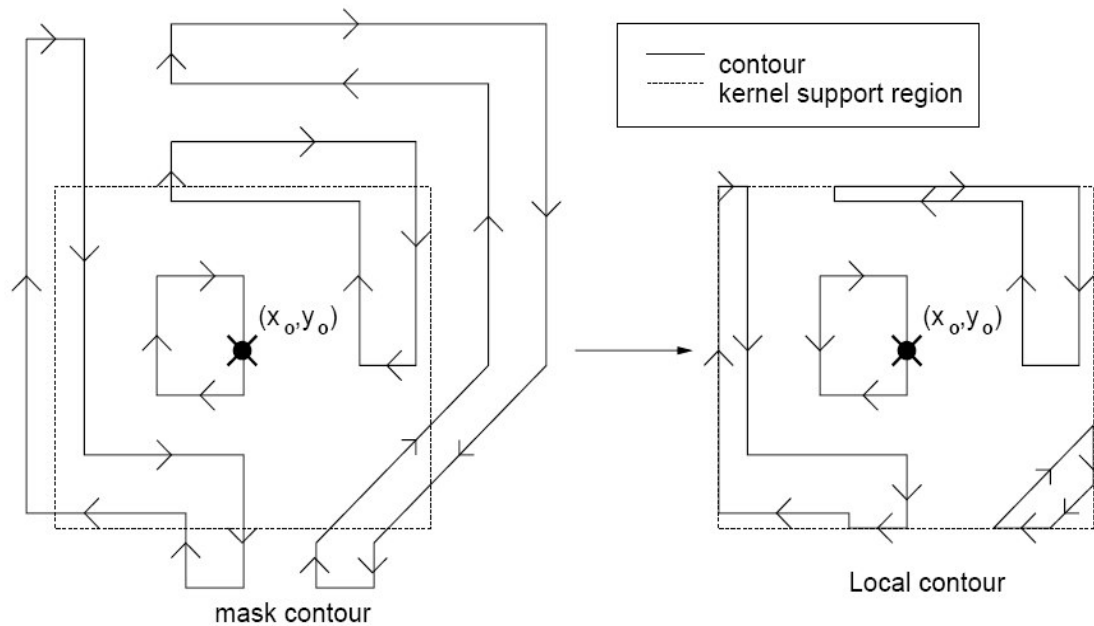
- ◆ In reality, for accurate simulation, the following corrections are needed:
  - Partially coherent light. Extend to Hopkin's model.
  - Incorporate effect of lens aberrations into pupil function  $P$ .
  - Effect of defocus. Add phase error to higher diffraction orders.



# Fast aerial image simulation

- ◆ Modern techniques by
  - › [Cobb]
  - › [Stirniman et. al]
  - › [Pati et. Al]
- ◆ Basic principle: Precompute convolutions and store for fast table lookup.
- ◆ Our approach is a variation of [Cobb].
- ◆ Precompute all possible upper rectangular convolutions within a support region.

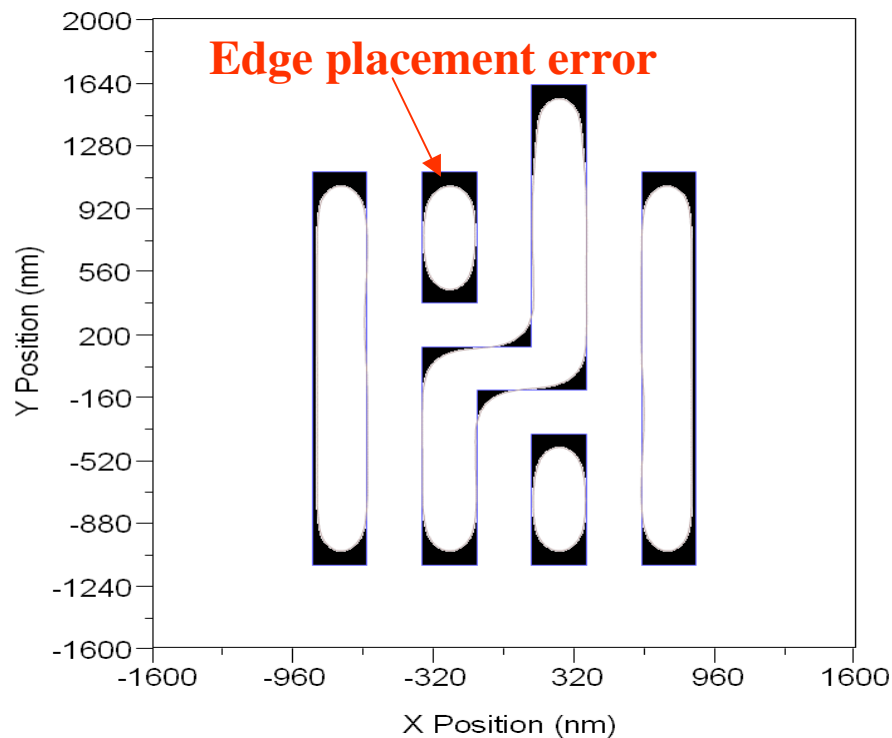
# (Cont'd)



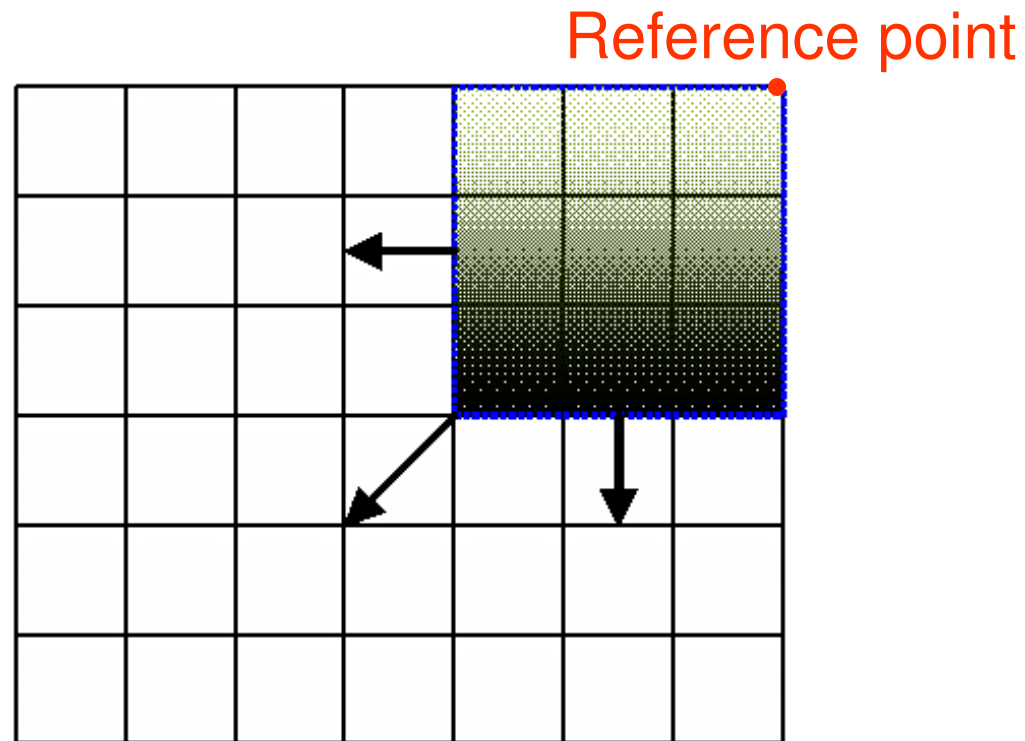
- Support region =  $1-4\mu\text{m}$  in perimeter or a multiple of resolution =  $?\text{/NA}$

# Edge Placement Error Map

- ◆ A concept similar to congestion or thermal hotspot
- ◆ Measurement of RET effort
- ◆ Work seamlessly with existing CAD flow

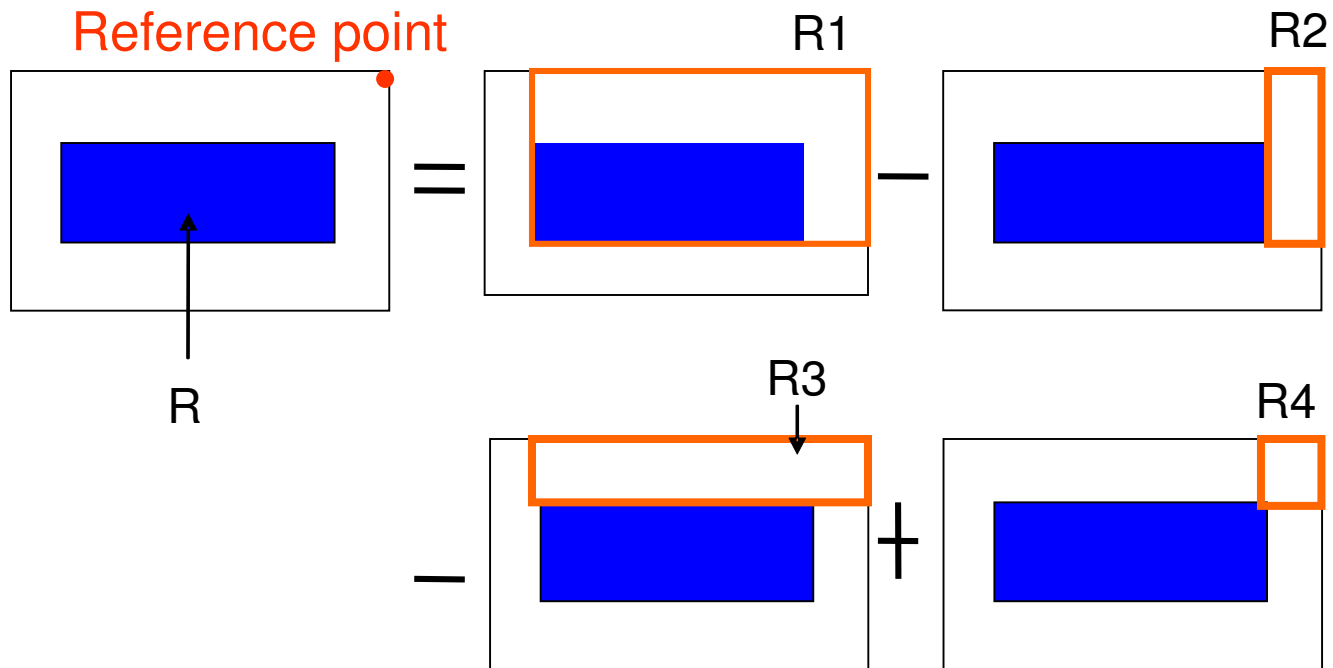


# Table Look-up



- Store convolution table for rectangles w.r.t the top-right reference point

# Table Look-up Example



$$\text{conv}(R) = \text{conv}(R1) - \text{conv}(R2) - \text{conv}(R3) + \text{conv}(R4)$$



## EPE Map

- ◆ Generate EPE for each “control point” (points that may have large edge placement errors) in design
- ◆ Each EPE control point has a ranked list of neighboring wires that contribute to the EPE
- ◆ Abstract a normalized EPE density for an entire routing segment

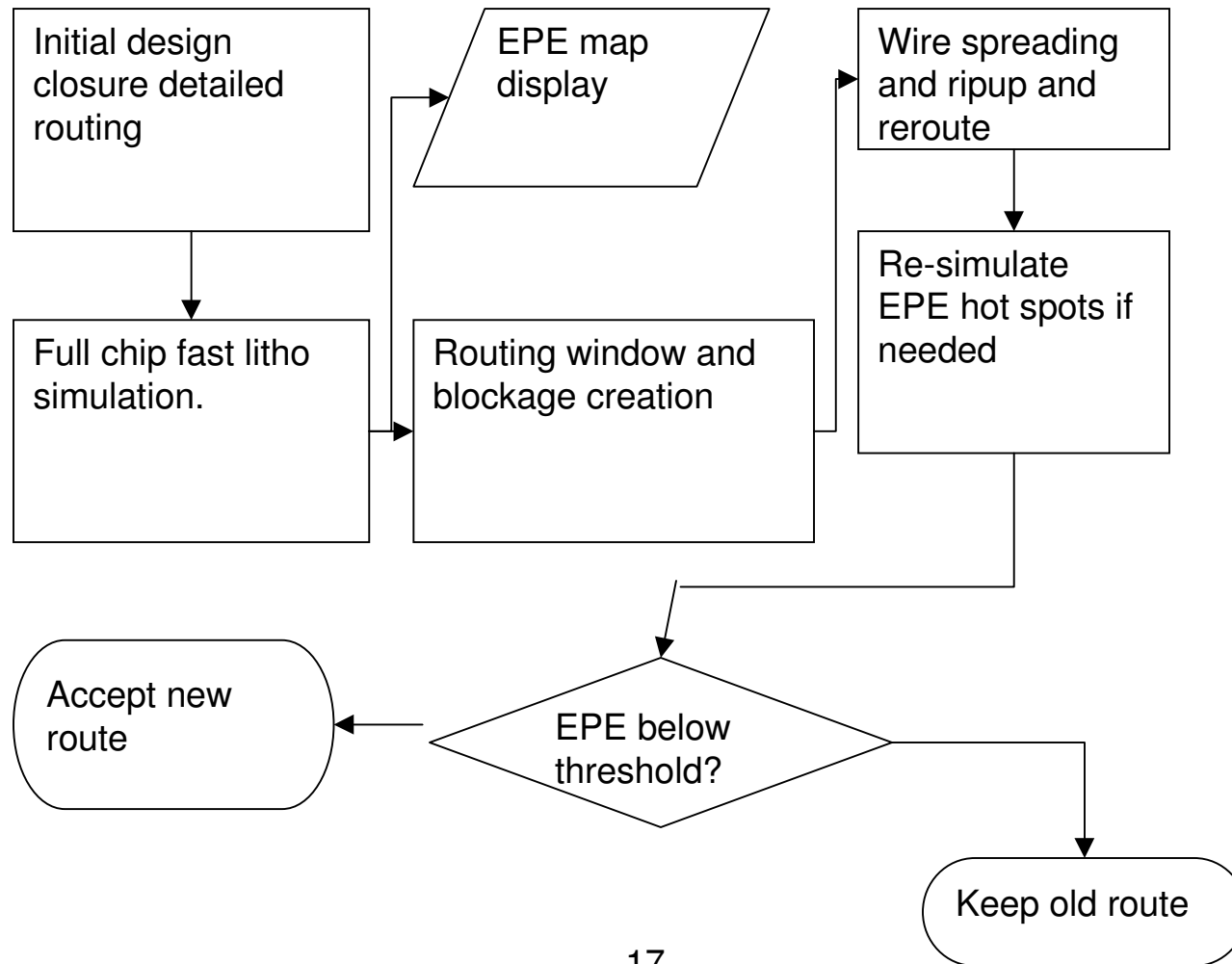
$$EPE_{avg} = \frac{\sum_{i=1}^N EPE_i}{N}$$



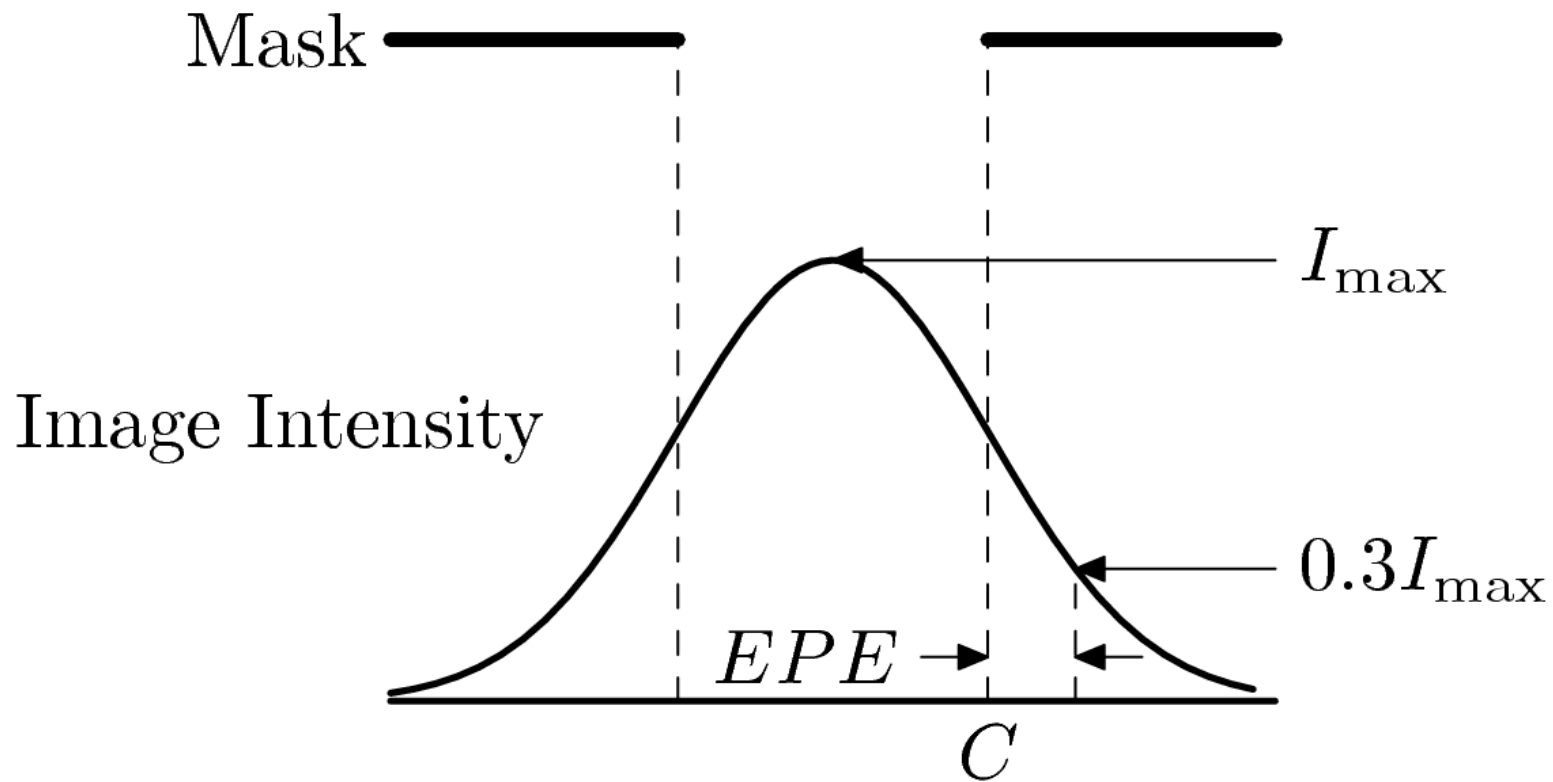
# RADAR: RET-Aware Detailed Routing

- ◆ Use EPE map to guide RADAR
  - › Do not need to run lithography simulations often
- ◆ Rip-up-and-reroute
  - › Focus on EPE **hotspots**
  - › Re-simulate EPE only if necessary (rerouted regions)
  - › Store EPE influencing neighbor list for router to avoid those neighbors with high EPE impacts
- ◆ Routing blockage generation and wire spreading
  - › Protect safe regions with low EPE

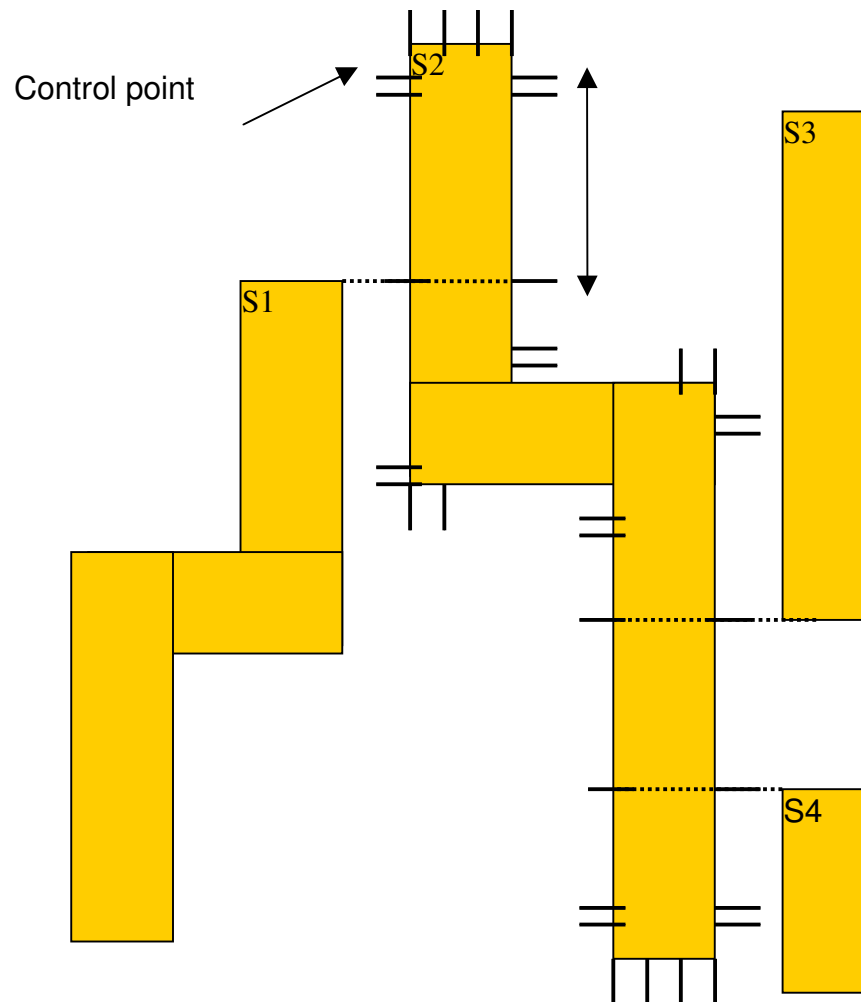
# EPE correction flow



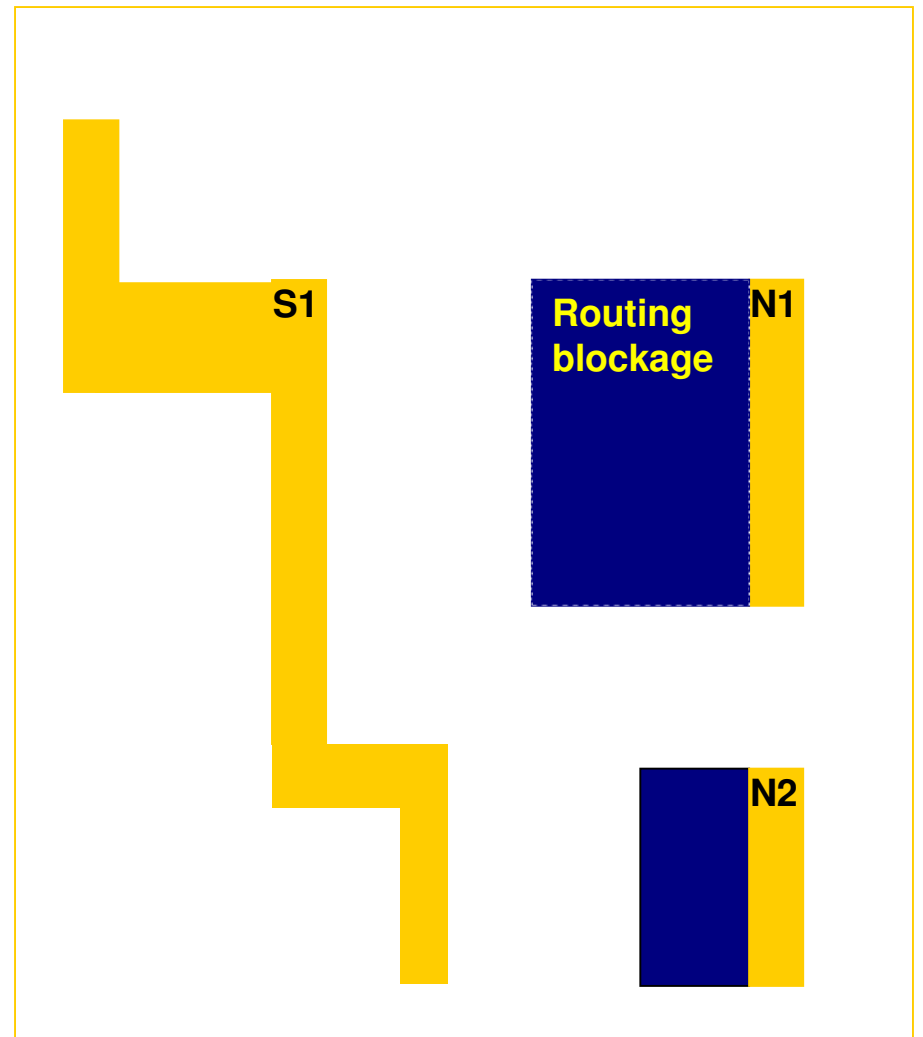
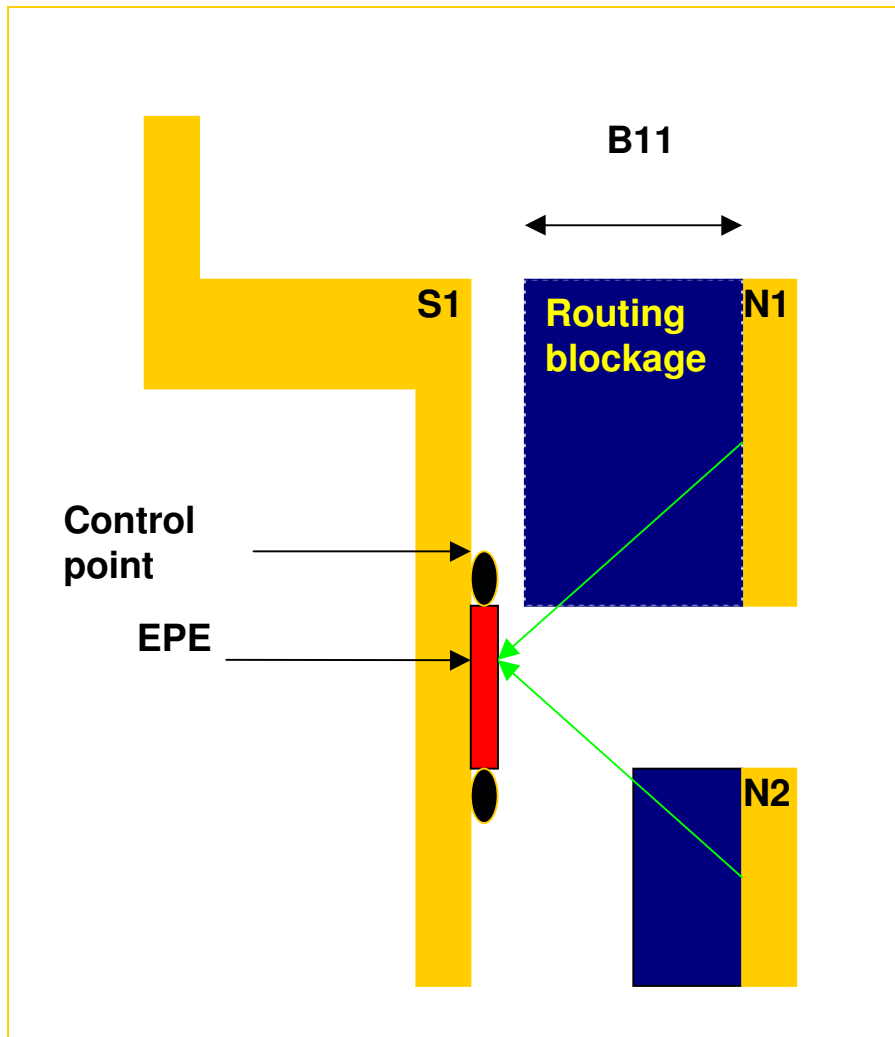
# EPE cutline computation

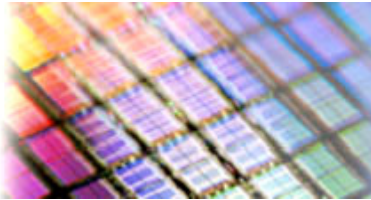


# Control point generation

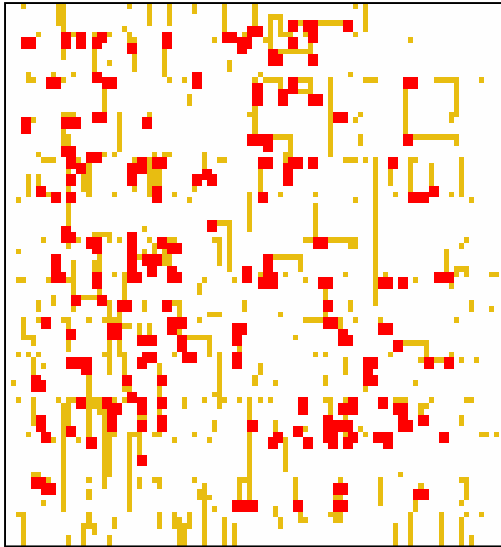


# Intelligent Ripup & Reroute

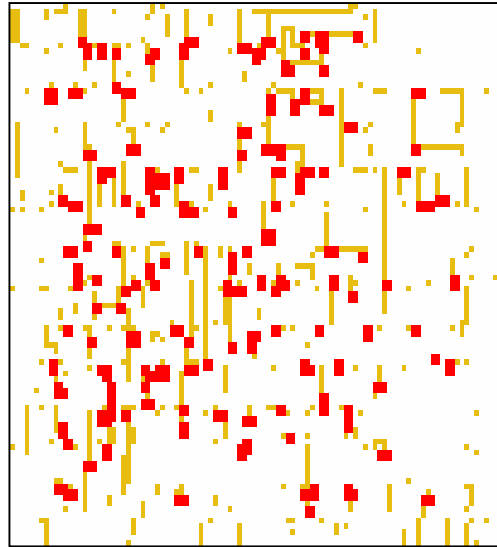




# Experimental Results on a 65nm Industry Design

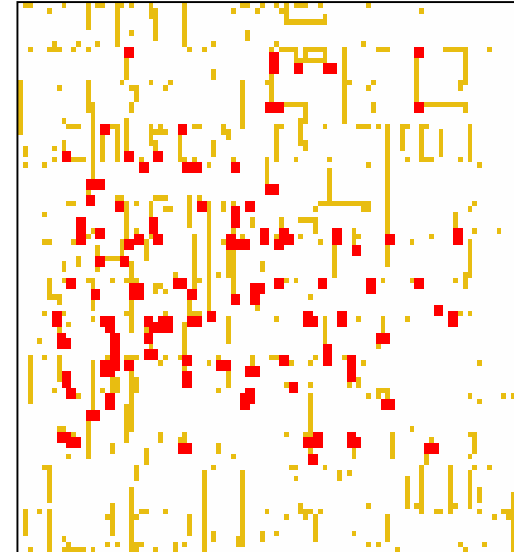


Initial routing (after design closure)



After wire spreading:

12% EPE reduction with 10% WL increase



After R&R:

40% EPE reduction  
5% WL increase



# Experimental Results

<b>Design</b>	<b>Original EPE</b>	<b>Spread EPE</b>	<b>R&amp;R EPE</b>	<b>Spread WL</b>	<b>R&amp;R WL</b>
<b>Ckt1</b>	<b>81</b>	<b>71</b>	<b>54</b>	<b>5%</b>	<b>2%</b>
<b>ckt2</b>	<b>720</b>	<b>612</b>	<b>468</b>	<b>20%</b>	<b>5%</b>
<b>ckt3</b>	<b>541</b>	<b>486</b>	<b>362</b>	<b>11%</b>	<b>5%</b>

- ◆ EPE reduced by 40%
  - › wirelength increased 5%



# Conclusions

- ◆ Raised Lithography modeling up to design implementation level.
- ◆ EPE map manufacturing effort metric.
- ◆ Two routing techniques to reduce EPE.
- ◆ RR using blockages showed promising results.
- ◆ Future research directions:
  - Further model speedup to enable correct-by-construction litho-friendly routing.
  - New manufacturing-friendly detailed routing algorithms.